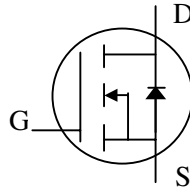




N-channel Enhancement-mode Power MOSFET

- Simple Drive Requirement**
- Low On-resistance**
- Fast Switching Performance**
- RoHS-compliant, Halogen-free**



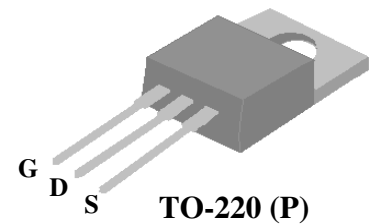
BV_{DSS}	75V
$R_{DS(ON)}$	4.8mΩ
I_D	170A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP95T07AGP-HF-3 is in the TO-220 through-hole package which is widely used in commercial and industrial applications where a small PCB footprint or an attached heatsink is required.

This device is well suited for low voltage applications such as DC/DC converters and DC motor drives.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	75	V
V_{GS}	Gate-Source Voltage	±20	V
I_D at $T_C=25^\circ C$	Continuous Drain Current (Silicon-limited)	170	A
I_D at $T_C=100^\circ C$	Continuous Drain Current (Silicon-limited)	120	A
I_D at $T_C=25^\circ C$	Continuous Drain Current (Package-limited)	120	A
I_{DM}	Pulsed Drain Current ¹	680	A
P_D at $T_C=25^\circ C$	Total Power Dissipation	300	W
T_{STG}	Storage Temperature Range	-55 to 175	°C
T_J	Operating Junction Temperature Range	-55 to 175	°C

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	0.5	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	°C/W

Ordering Information

AP95T07AGP-HF-3TB RoHS-compliant, halogen-free TO-220, shipped in tubes



Electrical Specifications at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	75	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=60A$	-	-	4.8	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=60A$	-	90	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=75V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=40A$	-	93	150	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=60V$	-	13	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	43	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=40V$	-	17	-	ns
t_r	Rise Time	$I_D=40A$	-	72	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	46	-	ns
t_f	Fall Time	$R_D=1\Omega$	-	93	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	3990	6380	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	920	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	345	-	pF
R_g	Gate Resistance	$f=1.0MHz$	-	1.2	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=40A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time ²	$I_S=40A, V_{GS}=0V$	-	70	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	160	-	nC

Notes:

1. Pulse width limited by maximum junction temperature.
2. Pulse test - pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.
 USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.
 APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED
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 RELIABILITY, FUNCTION OR DESIGN.



Typical Electrical Characteristics

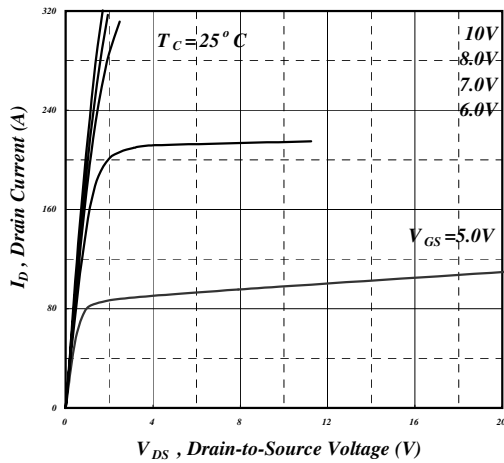


Fig 1. Typical Output Characteristics

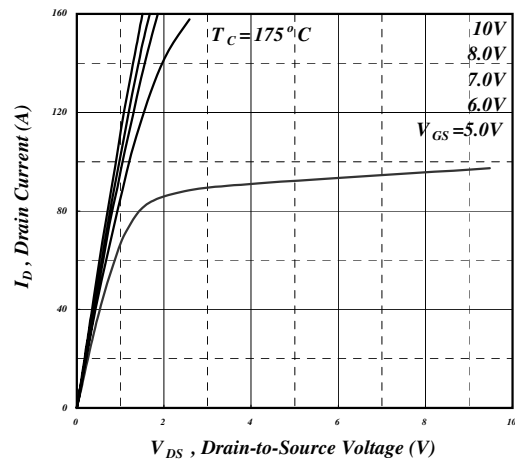


Fig 2. Typical Output Characteristics

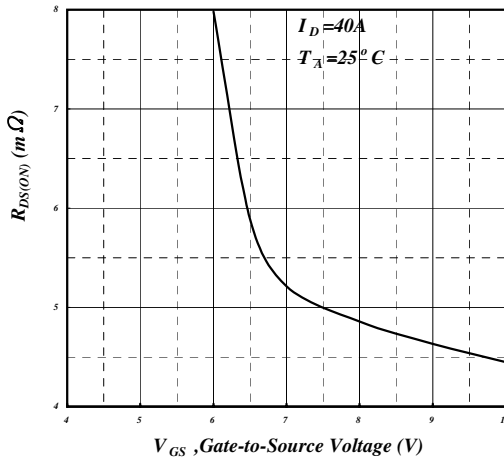


Fig 3. On-Resistance vs. Gate Voltage

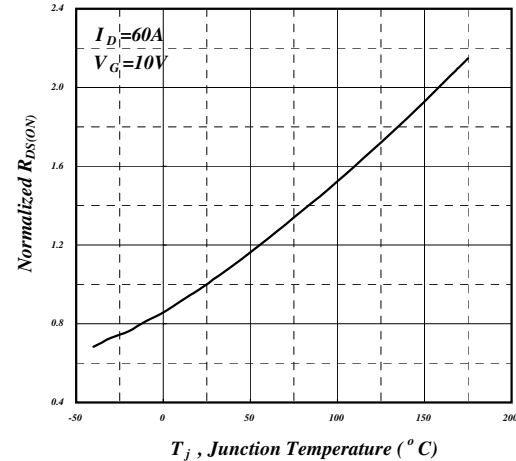


Fig 4. Normalized On-Resistance vs. Junction Temperature

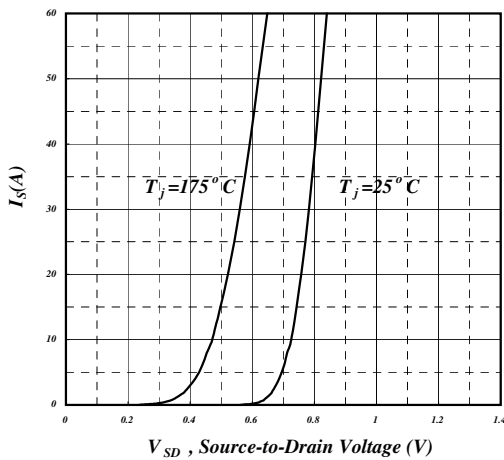


Fig 5. Forward Characteristic of Reverse Diode

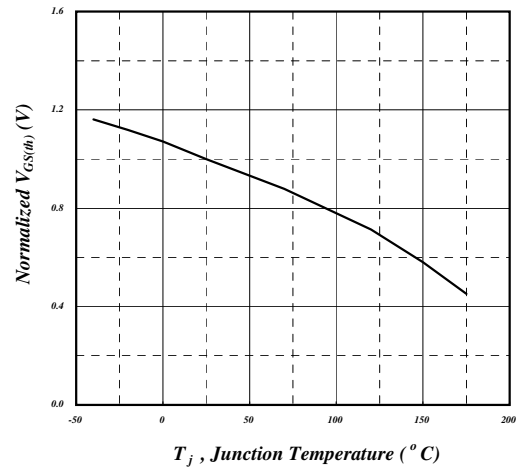


Fig 6. Gate Threshold Voltage vs. Junction Temperature



Typical Electrical Characteristics (cont.)

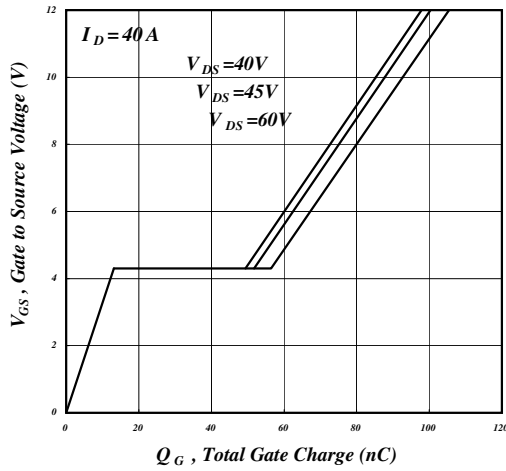


Fig 7. Gate Charge Characteristics

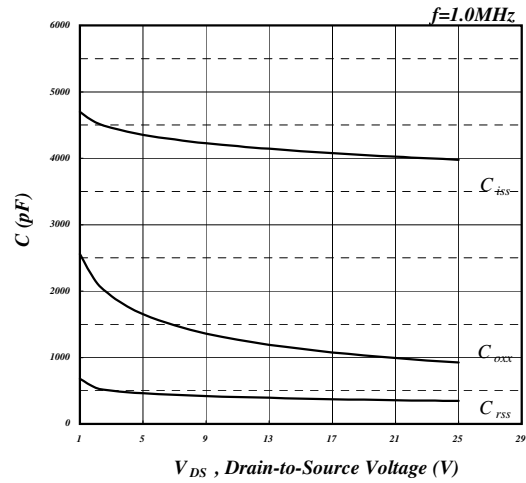


Fig 8. Typical Capacitance Characteristics

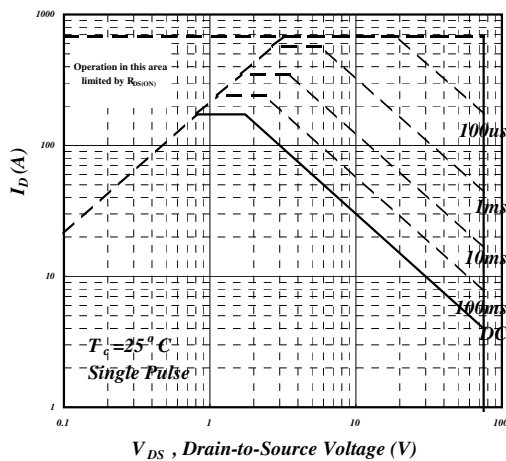


Fig 9. Maximum Safe Operating Area

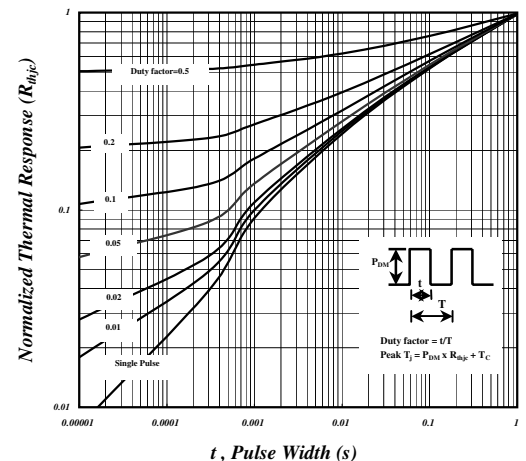


Fig 10. Effective Transient Thermal Impedance

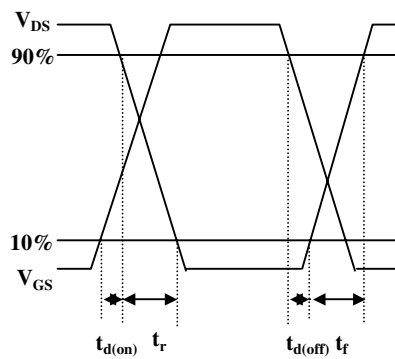


Fig 11. Switching Time Waveforms

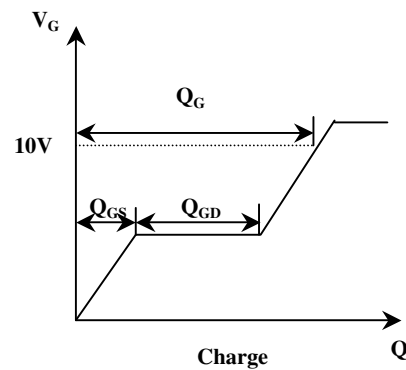
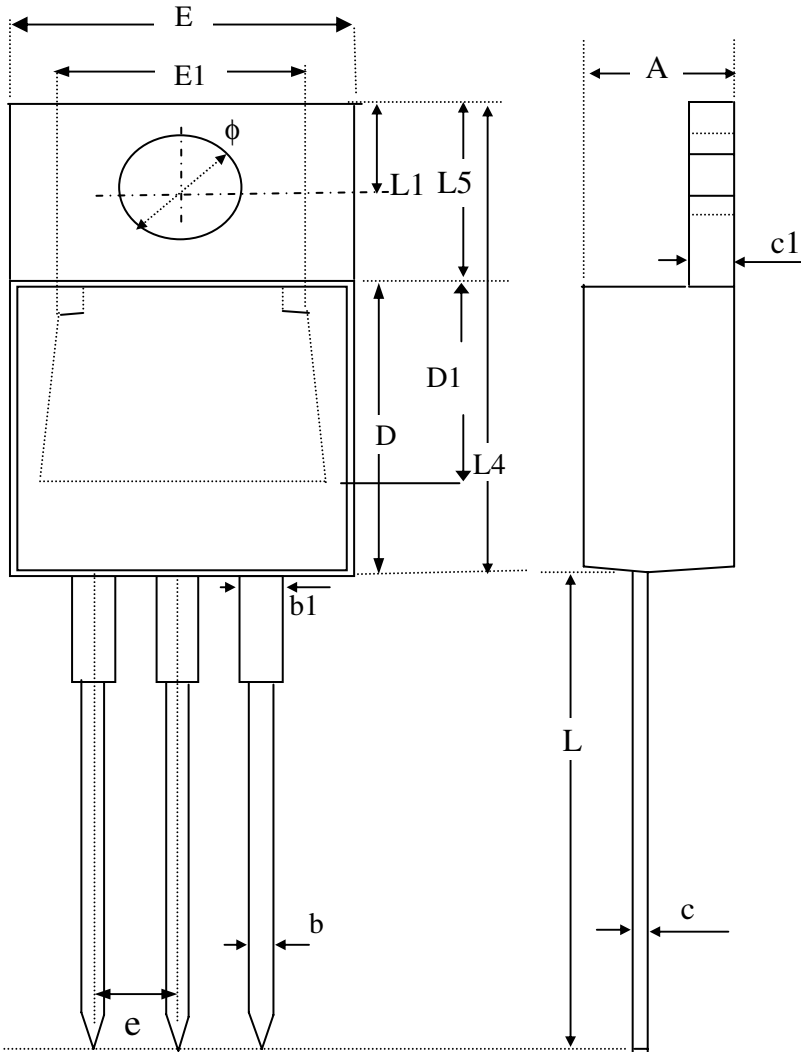


Fig 12. Gate Charge Waveform



Package Dimensions: TO-220



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.40	4.60	4.80
b	0.76	0.88	1.00
D	8.60	8.80	9.00
c	0.36	0.43	0.50
E	9.80	10.10	10.40
L4	14.70	15.00	15.30
L5	6.20	6.40	6.60
D1	5.10 REF.		
c1	1.25	1.35	1.45
b1	1.17	1.32	1.47
L	13.25	13.75	14.25
e	2.54 REF.		
L1	2.60	2.75	2.89
phi	3.71	3.84	3.96
E1	7.4 REF.		

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information:

